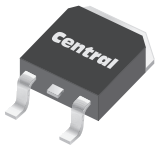
CSD-8M
CSD-8N

SURFACE MOUNT
SILICON CONTROLLED RECTIFIERS
8.0 AMP, 600 THRU 800 VOLT



DPAK CASE

Central Semiconductor Corp.

www.centralsemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CSD-8M and CSD-8N are epoxy molded SCRs designed for sensing circuit and control system applications.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: (T_C=25°C unless otherwise noted)

	SYMBOL	CSD-8M	CSD-8N	UNITS
Peak Repetitive Off-State Voltage	V_{DRM}, V_{RRM}	600	800	V
RMS On-State Current (T_C=90°C)	$I_{T(RMS)}$	8.0		A
Peak One Cycle Surge, t=10ms	I_{TSM}	80		A
I^2t Value for Fusing, t=10ms	I^2t	32		A^2s
Peak Gate Power, tp=10μs	P_{GM}	40		W
Average Gate Power Dissipation	$P_{G(AV)}$	1.0		W
Peak Forward Gate Current, tp=10μs	I_{FGM}	4.0		A
Peak Forward Gate Voltage, tp=10μs	V_{FGM}	16		V
Peak Reverse Gate Voltage, tp=10μs	V_{RGM}	5.0		V
Critical Rate of Rise of On-State Current	di/dt	50		A/μs
Operating Junction Temperature	T_J	-40 to +125		°C
Storage Temperature	T_{stg}	-40 to +150		°C

ELECTRICAL CHARACTERISTICS: (T_C=25°C unless otherwise noted)

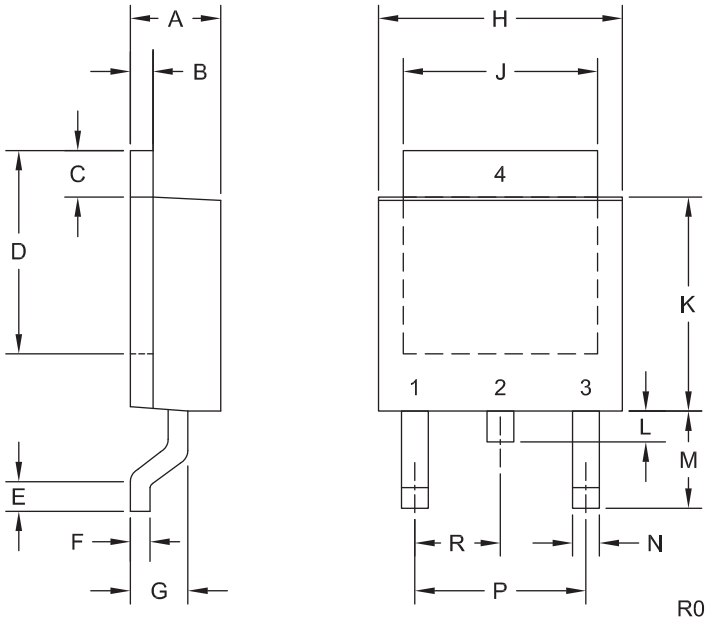
SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{DRM}, I_{RRM}	Rated V_{DRM}, V_{RRM}			10	μA
I_{DRM}, I_{RRM}	Rated V_{DRM}, V_{RRM}, T_C=125°C			2.0	mA
I_{GT}	V_D=12V, R_L=10Ω		3.0	15	mA
I_H	I_T=100mA		7.3	20	mA
V_{GT}	V_D=12V, R_L=10Ω		0.9	1.5	V
V_{TM}	I_{TM}=16A, tp=380μs		1.3	1.8	V
dv/dt	V_D=$^2/_3$ V_{DRM}, T_C=125°C	200			V/μs

R2 (21-January 2013)

CSD-8M
CSD-8N

SURFACE MOUNT
SILICON CONTROLLED RECTIFIERS
8.0 AMP, 600 THRU 800 VOLT

DPAK CASE - MECHANICAL OUTLINE



R0

LEAD CODE:
1) Cathode
2) Anode
3) Gate
4) Anode

MARKING:
FULL PART NUMBER

DIMENSIONS				
	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
A	0.083	0.108	2.10	2.75
B	0.016	0.032	0.40	0.81
C	0.035	0.063	0.89	1.60
D	0.203	0.228	5.15	5.79
E	0.020	-	0.51	-
F	0.018	0.024	0.45	0.60
G	0.051	0.071	1.30	1.80
H	0.248	0.268	6.30	6.81
J	0.197	0.217	5.00	5.50
K	0.209	0.245	5.30	6.22
L	0.025	0.040	0.64	1.02
M	0.090	0.115	2.30	2.91
N	0.012	0.045	0.30	1.14
P	0.180		4.60	
R	0.090		2.30	

DPAK (REV: R0)

R2 (21-January 2013)